

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

TK10Q60W, ITK10Q60W

• FEATURES

- Low drain-source on-resistance: R⊳s(on) ≤0.43Ω.
- Enhancement mode:

Vth =2.7 to 3.7V (V_{DS} = 10 V, I_D=0.5mA)

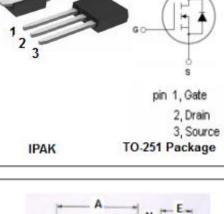
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

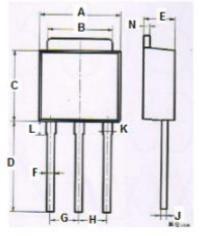
Switching Voltage Regulators

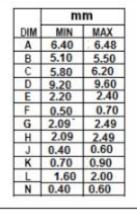
• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT				
V _{DSS}	Drain-Source Voltage	600	V				
V _{GS}	Gate-Source Voltage	±30	V				
ID	Drain Current-Continuous	9.7	А				
I _{DM}	Drain Current-Single Pulsed	38.8	А				
PD	Total Dissipation @T _c =25°C	80	W				
Tj	Max. Operating Junction Temperature	150	°C				
T _{stg}	Storage Temperature	-55~150	°C				



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• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT		
Rth(ch-c)	Channel-to-case thermal resistance	1.57	°C/W		
Rth(ch-a)	Rth(ch-a) Channel-to-ambient thermal resistance		°C/W		

1



isc N-Channel MOSFET Transistor TK10Q6

TK10Q60W, ITK10Q60W

ELECTRICAL CHARACTERISTICS

 $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =10mA	600			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =10V; I _D =0.5mA	2.7		3.7	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =4.9A			0.43	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} =0V			±1	μA
IDSS	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			10	μA
V _{SDF}	Diode forward voltage	I _{DR} =9.7A, V _{GS} = 0 V			1.7	v

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2